



ECH8620 — N-Channel and P-Channel Silicon MOSFETs

General-Purpose Switching Device Applications

Features

- The ECH8620 incorporates an N-channel MOSFET and a P-channel MOSFET that feature low ON-resistance and ultrahigh-speed switching, thereby enabling high-density mounting.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	N-channel	P-channel	Unit
Drain-to-Source Voltage	V _{DSS}		100	-100	V
Gate-to-Source Voltage	V _{GSS}		±20	±20	V
Drain Current (DC)	I _D		2	-1.5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	12	-12	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² ×0.8mm) 1unit	1.3		W
Total Dissipation	P _T	Mounted on a ceramic board (900mm ² ×0.8mm)	1.5		W
Channel Temperature	T _{ch}		150		°C
Storage Temperature	T _{stg}		-55 to +150		°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[N-channel]						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0V	100			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =1A	1.6	2.7		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =1A, V _{GS} =10V		200	260	mΩ
	R _{DS(on)2}	I _D =0.5A, V _{GS} =4V		230	325	mΩ

Marking : FN

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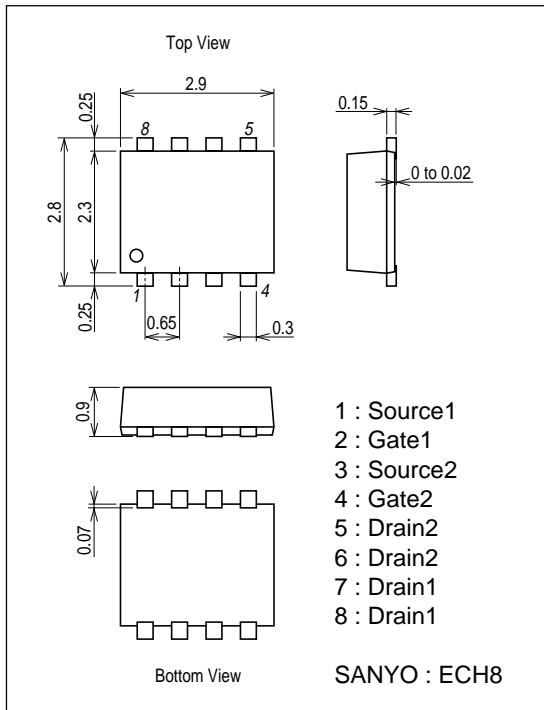
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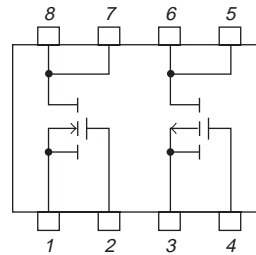
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		650		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		42		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		29		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		11.5		ns
Rise Time	t _r	See specified Test Circuit.		4.9		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		67		ns
Fall Time	t _f	See specified Test Circuit.		23		ns
Total Gate Charge	Q _g	V _{DS} =50V, V _{GS} =10V, I _D =2A		13.8		nC
Gate-to-Source Charge	Q _{gs}	V _{DS} =50V, V _{GS} =10V, I _D =2A		2.1		nC
Gate-to-Drain "Miller" Charge	Q _{gd}	V _{DS} =50V, V _{GS} =10V, I _D =2A		3		nC
Diode Forward Voltage	V _{SD}	I _S =2A, V _{GS} =0V		0.80	1.2	V
[P-channel]						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =-1mA, V _{GS} =0V	-100			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-1A	1.8	3.1		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-1A, V _{GS} =-10V		400	520	mΩ
	R _{DS(on)2}	I _D =-0.5A, V _{GS} =-4V		460	645	mΩ
Input Capacitance	Ciss	V _{DS} =-20V, f=1MHz		630		pF
Output Capacitance	Coss	V _{DS} =-20V, f=1MHz		41		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-20V, f=1MHz		38		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		10.0		ns
Rise Time	t _r	See specified Test Circuit.		5.5		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		91		ns
Fall Time	t _f	See specified Test Circuit.		27		ns
Total Gate Charge	Q _g	V _{DS} =-50V, V _{GS} =-10V, I _D =-1.5A		14.7		nC
Gate-to-Source Charge	Q _{gs}	V _{DS} =-50V, V _{GS} =-10V, I _D =-1.5A		1.6		nC
Gate-to-Drain "Miller" Charge	Q _{gd}	V _{DS} =-50V, V _{GS} =-10V, I _D =-1.5A		2.8		nC
Diode Forward Voltage	V _{SD}	I _S =-1.5A, V _{GS} =0V		-0.8	-1.2	V

Package Dimensions

unit : mm (typ)
7011A-001



Electrical Connection



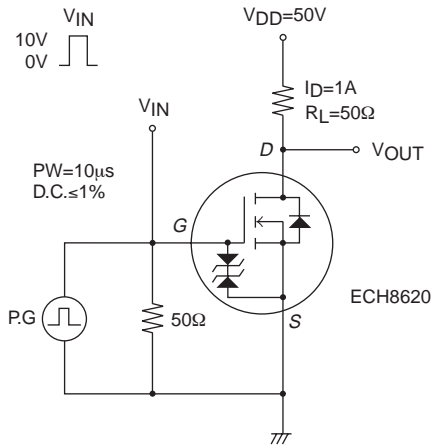
- 1 : Source1
- 2 : Gate1
- 3 : Source2
- 4 : Gate2
- 5 : Drain2
- 6 : Drain2
- 7 : Drain1
- 8 : Drain1

Top view

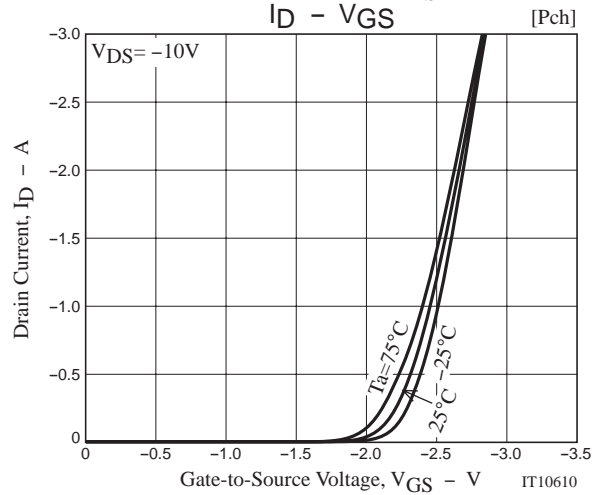
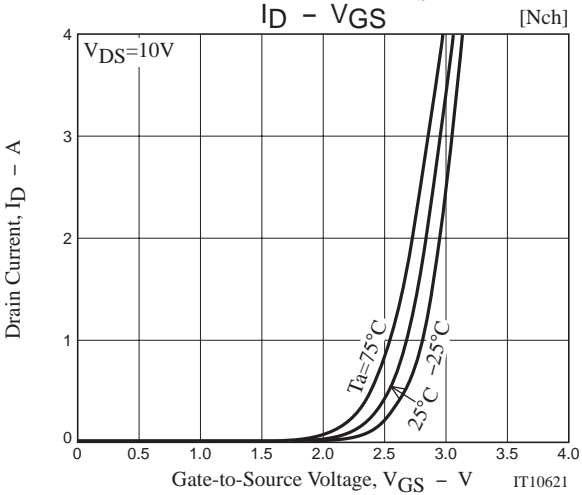
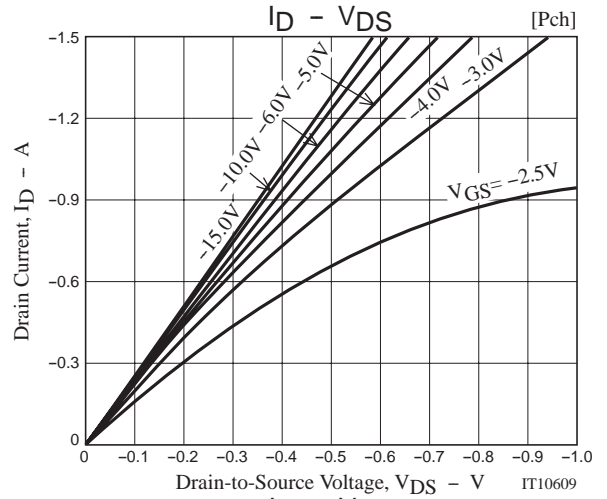
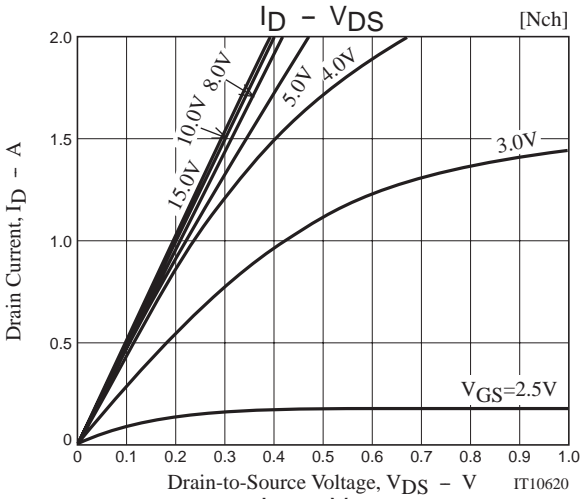
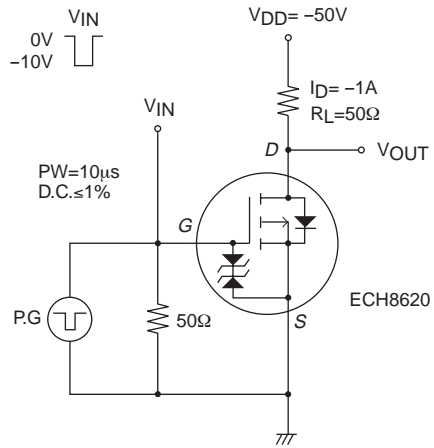
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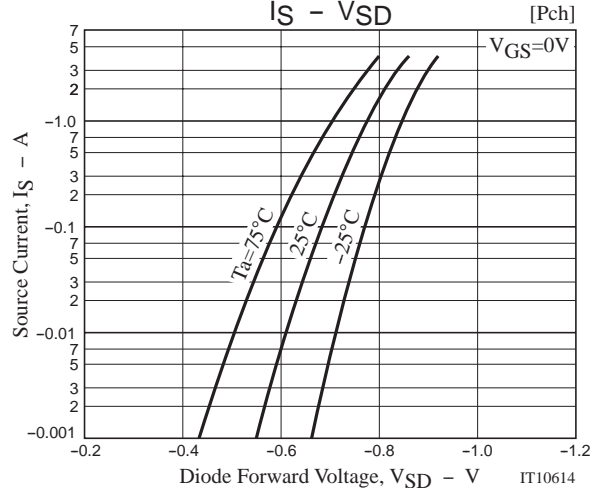
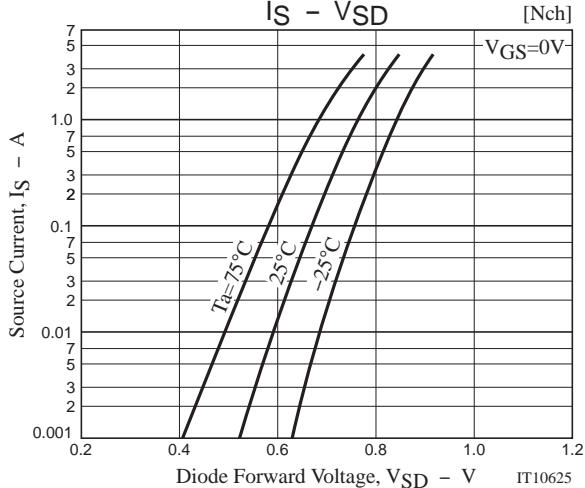
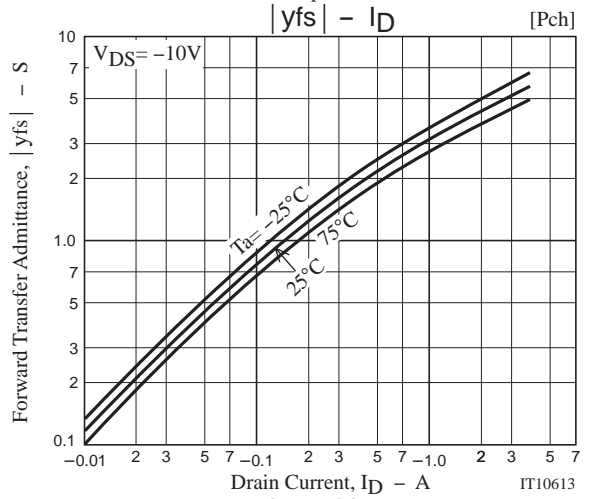
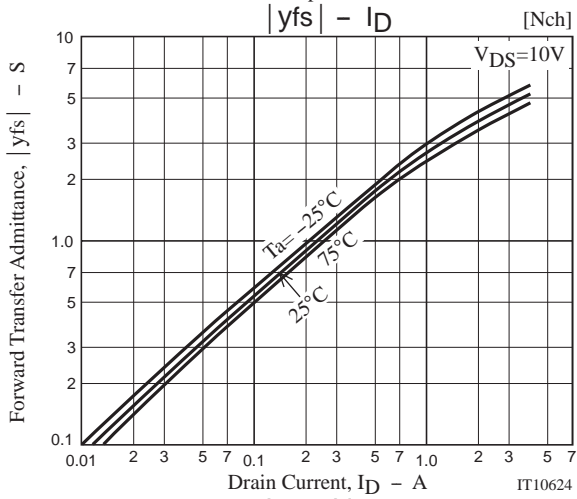
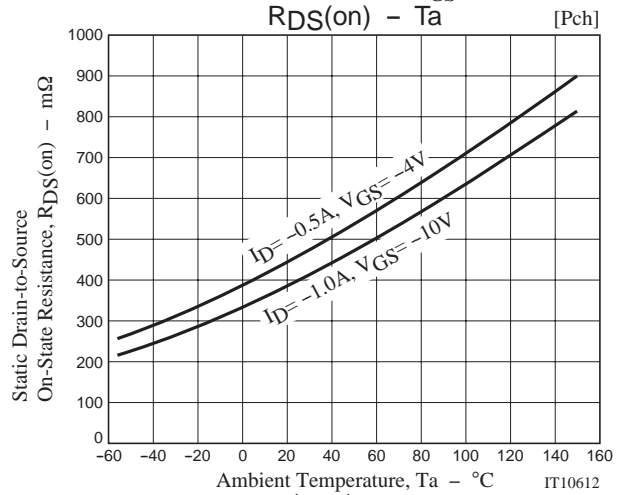
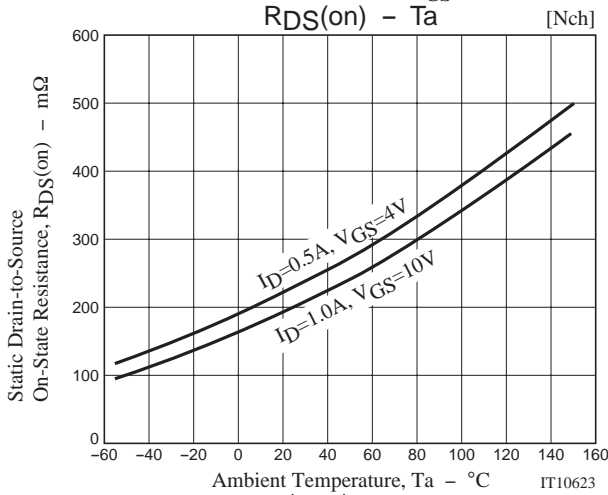
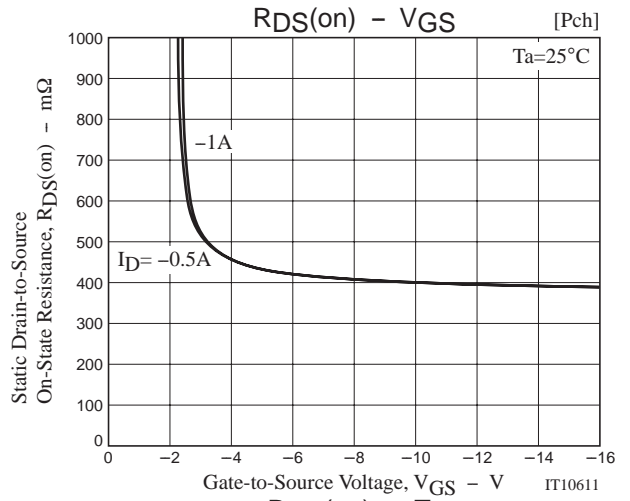
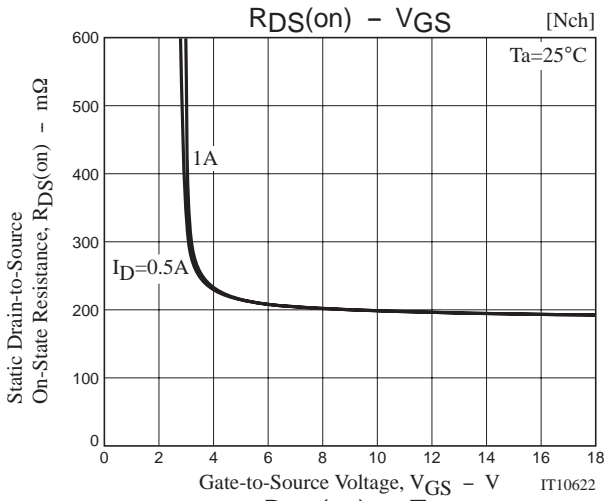
Switching Time Test Circuit

[N-channel]

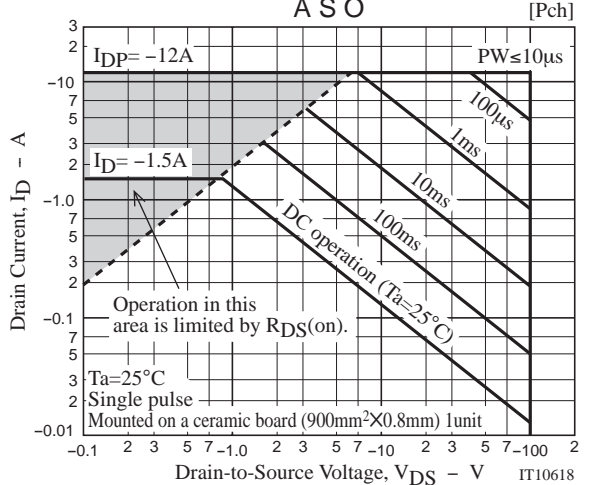
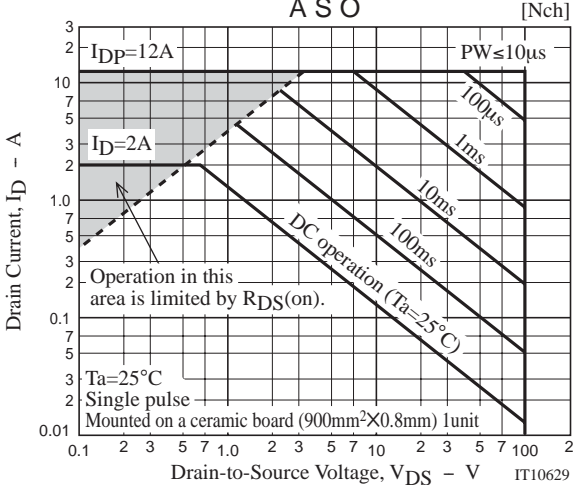
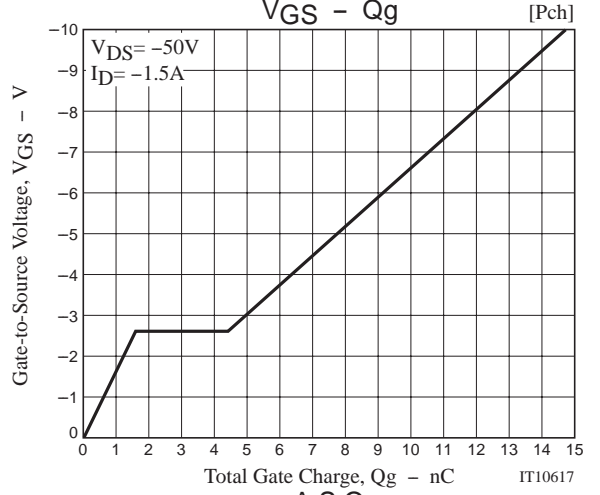
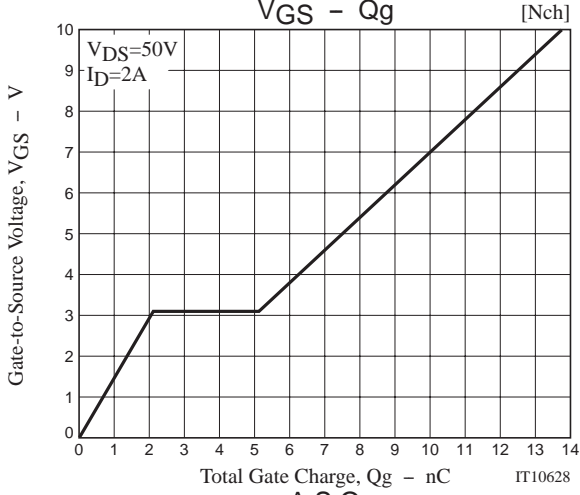
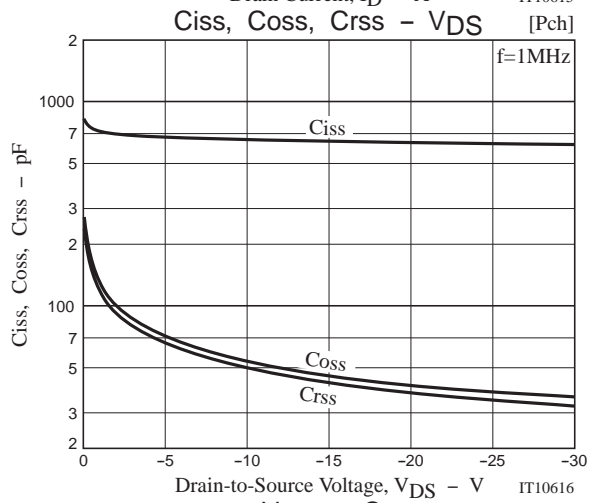
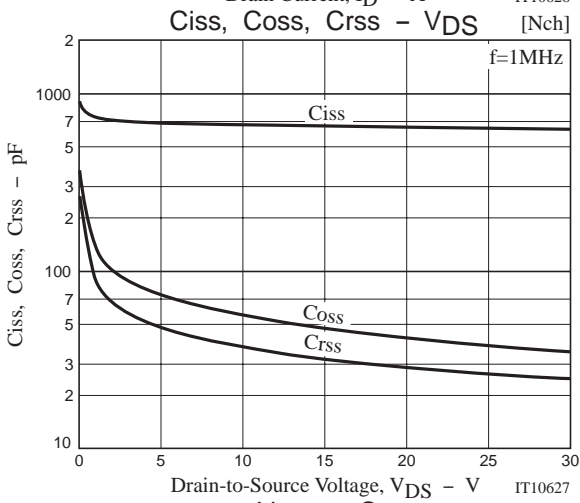
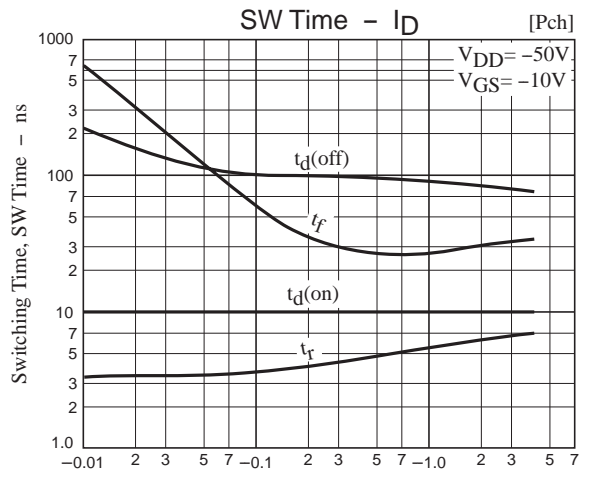
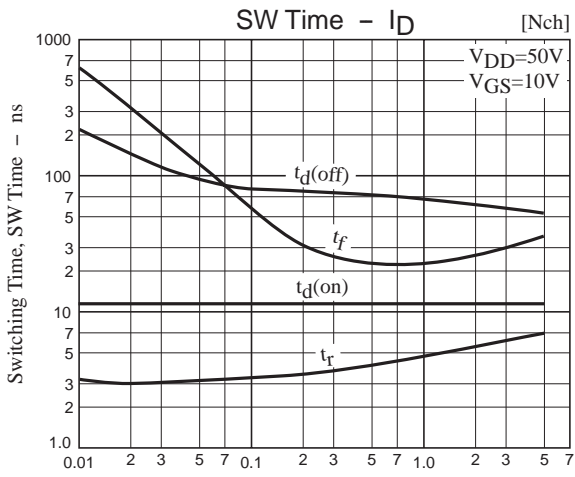


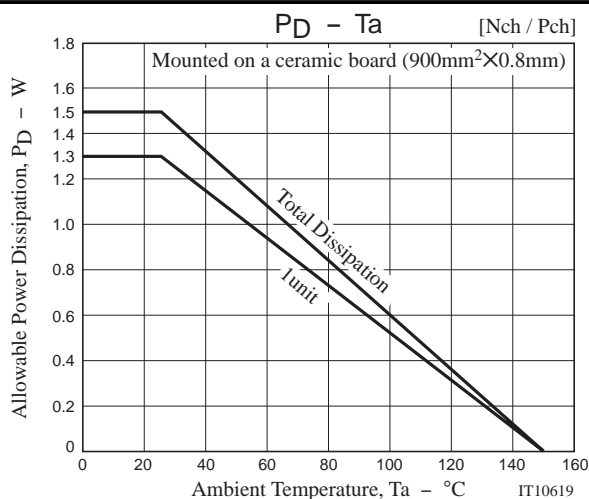
[P-channel]





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Note on usage : Since the ECH8620 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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